



MicroLED Display Integration on 300mm Advanced CMOS Platform

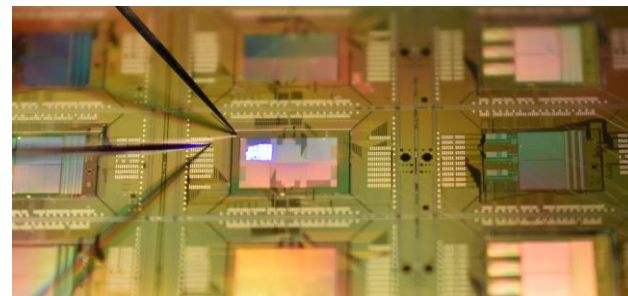


Soeren Steudel, CTO

COMPANY OVERVIEW



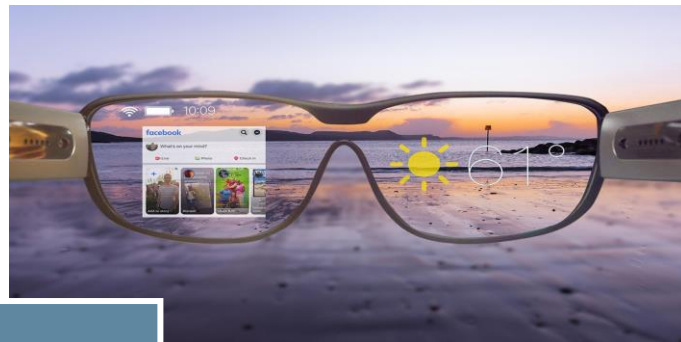
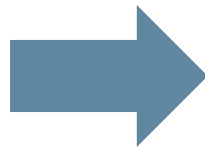
- Company:** Micledi Microdisplays
- Vertical:** Consumer Electronics, AR
- Product:** MicroLED Displays
- Business model:** B2B Fabless Hardware Component Sales
- Technology IP:** Spin-out of IMEC in 2019
- USP:** Size, Power Efficiency, Image Quality
- Financials:** Pre-Revenue
- Investment:** >10MEUR



MARKET DEVELOPMENT

Today: Large, Heavy, Expensive, Poor Image

Tomorrow: Compact, Attractive, Low-cost, Low Power, Beautiful Image



The dream

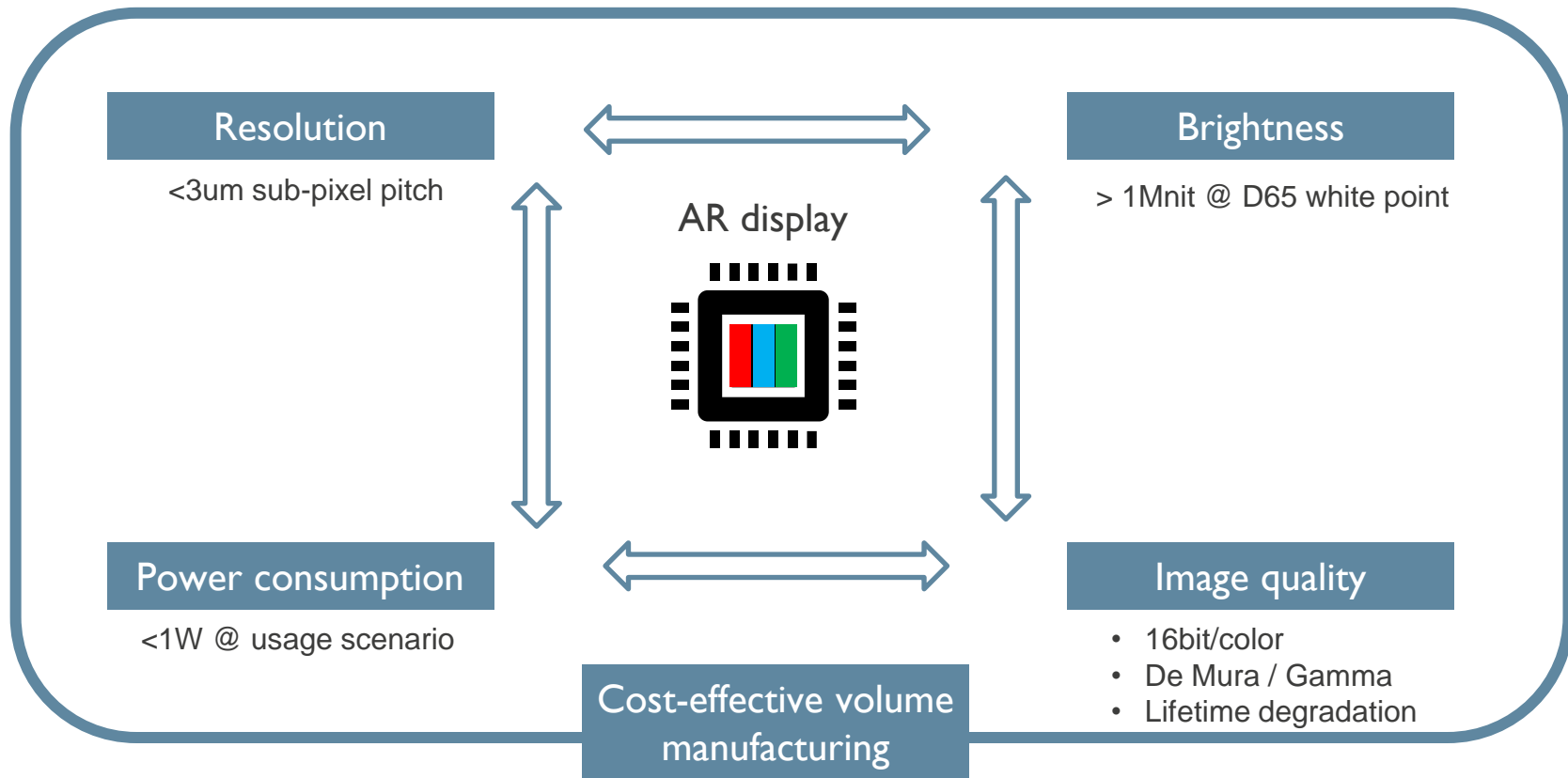


Cfr. MagicLeap

The big elephant in the room. How to solve:

- Accommodation and Convergence
- Occlusion

TECHNICAL PROBLEM STATEMENT



STATE-OF-THE-ART

AR/CMOS μ LED display (excl. μ LED flat panel displays)



Companies with own known development efforts:

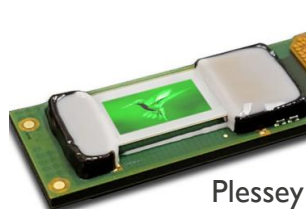
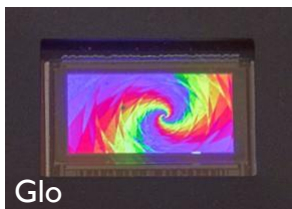
	Start-up1	Company1	Start-up2	Company2	Start-up3	Start-up4	R&D1	Start-up5
CMOS integration	D2W	D2W	Subsequent 3D	W2W	polysilicon TFT	D2W / W2W	subsequent 3D	D2W
Color creation	Downconversion	RGB transfer	Combiner	n.a.	Downconversion	Downconversion	n.a.	Stacked QW
Wafer size LED [mm]	100	100	100	200	150	200	200	150
Wafer size CMOS [mm]	200	200	200	200	150	200	200	200
Wafer level optics solution	No	Yes	Yes	Yes	No	No	No	Yes
Manufacturability / yield / cost								
Issues with image quality								
Issues with brightness								
Issues with resolution								

	Company3	Start-up6	Company4	Start-up7	Company5	MICLEDI	Company6
CMOS integration	D2W and W2W	subsequent 3D	D2W	D2W	D2W	W2W	D2W
Color creation	Combiner	n.a.	Downconversion	RGB transfer	RGB NW growth	Combiner	n.a.
Wafer size LED [mm]	150/200	n.a.	150	n.a.	n.a.	300	n.a.
Wafer size CMOS [mm]	200	n.a.	200	n.a.	200	300	n.a.

Large competition
 Large investment
 Very different technology

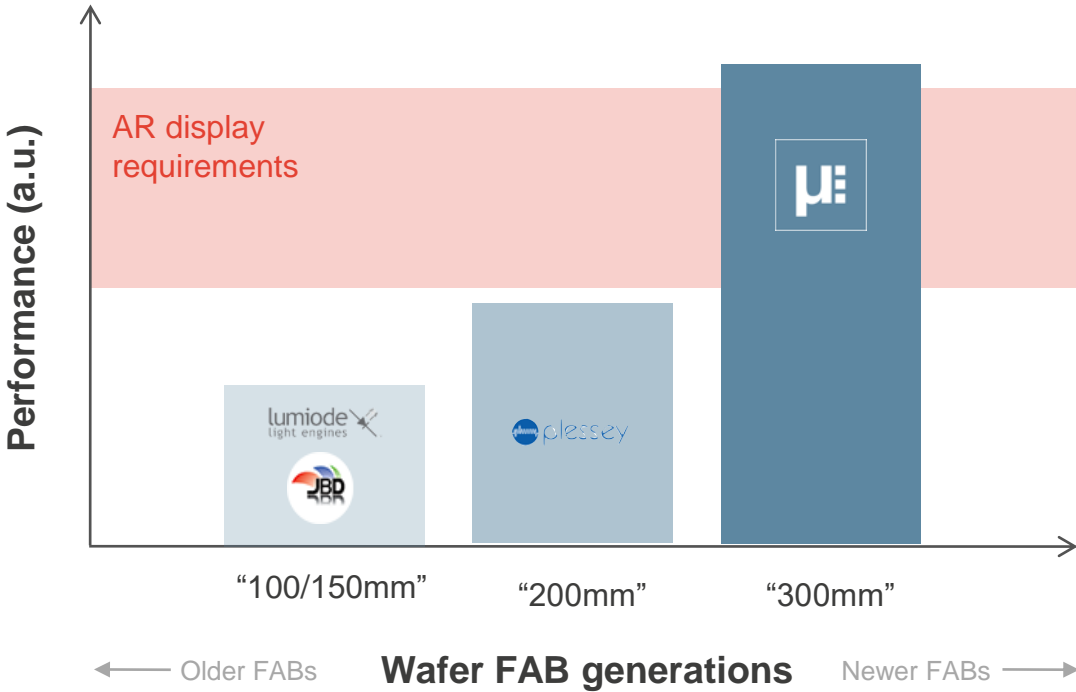
- CMOS integration (4x routes)
- RGB LED (8x routes)
- Optics (3-4x routes)
- Driving and compensation (xx routes)

- Aledia
- Compound Photonics
- EpiPix
- META
- Lumiodo
- Lumens
- MojoVision
- NS Nanotech
- Plessey
- Ostendo
- Raxium
- Raysolve
- JBD
- Sharp
- VueReal
- ..many more



UNIQUENESS OF MICLEDI TECHNOLOGY

LEVERAGING MOST ADVANCED EQUIPMENT IN SEMI INDUSTRY



MicroLED with AR specs is **only possible in advanced 300mm (foundry) manufacturing**

- advanced node driving ASIC (<45nm)
- advanced litho for wfr level optics (CD<100nm, overlay<20nm)
- tight W2W hybrid bonding overlay specs (<200nm)

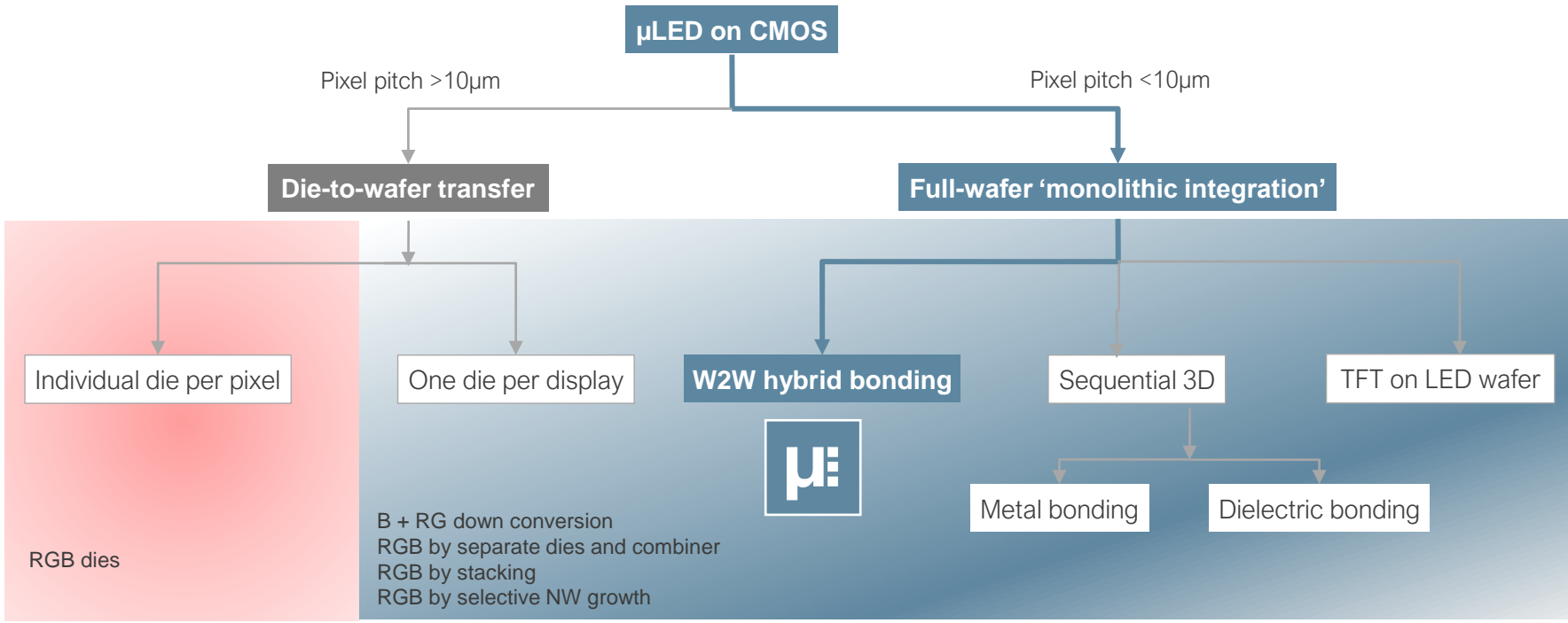
Requires **dedicated technology development**

Uniqueness: Micledi is the only startup for microLED in 300mm

*Full flow development @imec with standard high-throughput automatic production tools

INTEGRATION CHALLENGES

MICRO-LED ON CMOS



RGB COLOR

VS SPECS FOR AR WAVEGUIDE OPTICS



	RGB pixel level die assembly	RBG dies and combiner optics	RG down conversion	Selective RGB templated growth (e.g., NW)
RGB color	pixel-by-pixel row-by-row	die-by-die	pixel-by-pixel	pixel-by-pixel
Pixel density	Red	Green	Yellow	Yellow
Brightness	Green	Green	Red	Green with diagonal stripes
Yield	Red	Green	Green	Red
System cost	Yellow	Yellow	Green	Green
Display size	Yellow	Green	Green	Green with diagonal stripes
Image quality	Green	Green	Red	Yellow
Lifetime	Green	Green	Red	Yellow

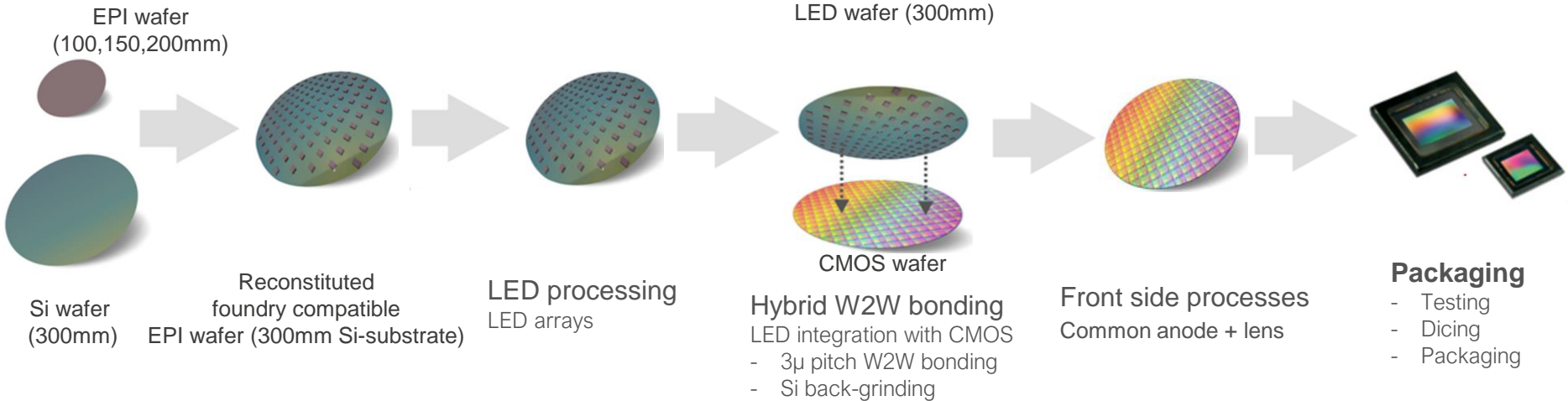
Alternative RGB routes explored by different companies

- Stacked RGB QW (W2W bonding)
- Stacked RGB QW (epi overgrowth/Multi-contact)
- RGB etched nanopillar

1. The display size is limited by the pixel density. Added constraint is CMOS driver size.
2. RGB die-by-die and RGB pixel-by-pixel have the same size constraints.
3. CMOS power consumption scales with number of pixel and image quality.
4. LED power consumption scales with emissive area.

LED PROCESS FLOW FOR W2W BONDING

HIGH LEVEL OVERVIEW



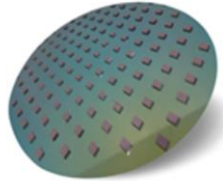
Issues solved by MICLEDI	<ul style="list-style-type: none"> • Defectivity • No 300mm epi • Residual stress 	<ul style="list-style-type: none"> • CMOS compatible LED process flow 	<ul style="list-style-type: none"> • CMOS/LED tight pitch integration 	<ul style="list-style-type: none"> • LED performance • Beam shaping 	<ul style="list-style-type: none"> • Driving • Calibration
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300MM EPI SOLUTION

EPI WAFER RECONSTITUTION

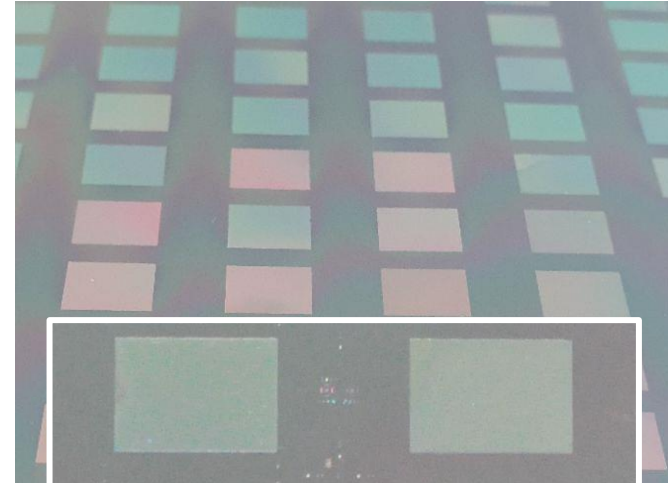
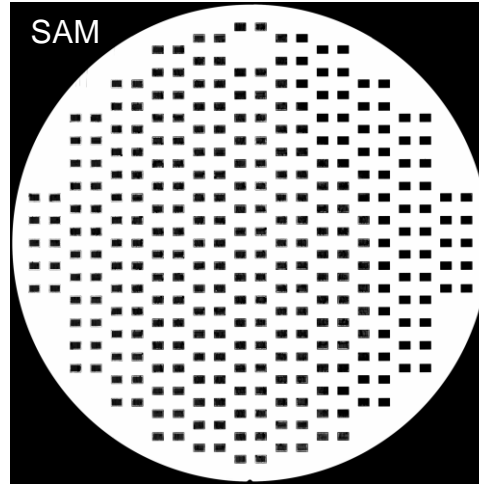


EPI wafer (GaN, AlInGaP)
(100/150/200mm)



Foundry compatible
LED on 300mm

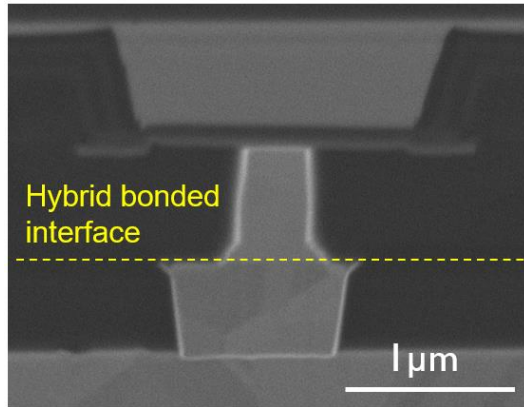
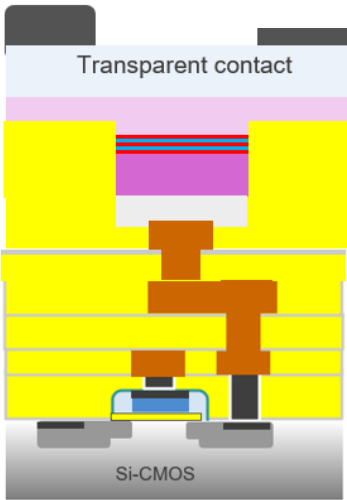
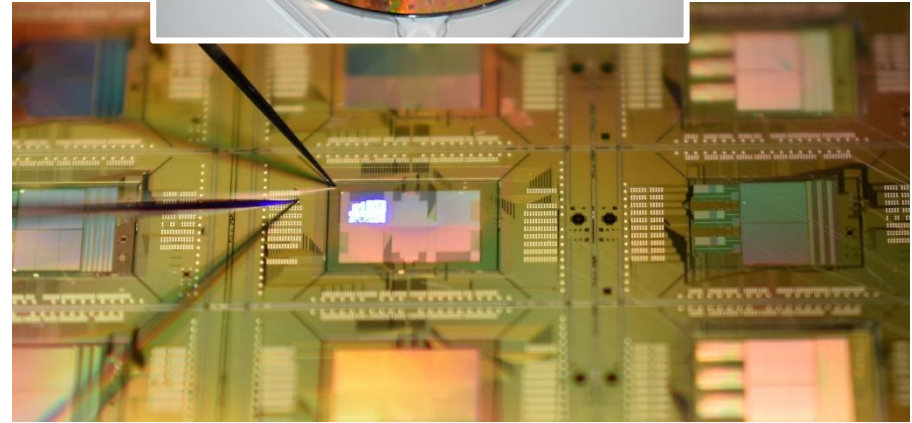
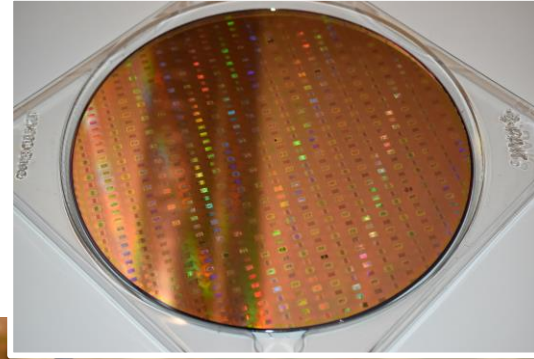
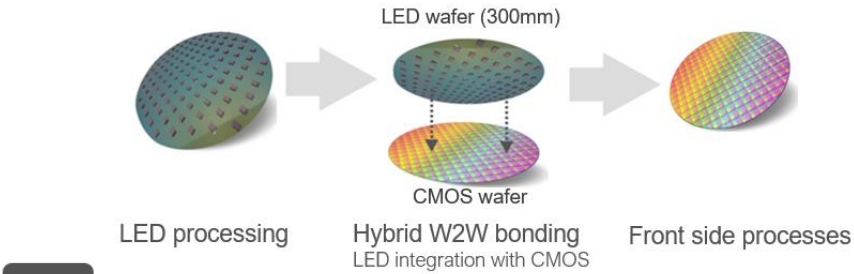
Si wafer
(300mm)



- Planarized 300mm reconstituted epi-wafer on standard Si-wafer
- Die attach yield up to 100%
- Pre-selection of epi dies for low-defectivity & optical properties possible
- Wafer bow < 20 μ m and no residual stress
- n/QW/p LED epi – layer with buffer removal < 1.5 μ m thickness
- Planarization verified by W2W bonding

DISPLAY INTEGRATION

300MM CMOS FAB COMPATIBLE PROCESS FLOW

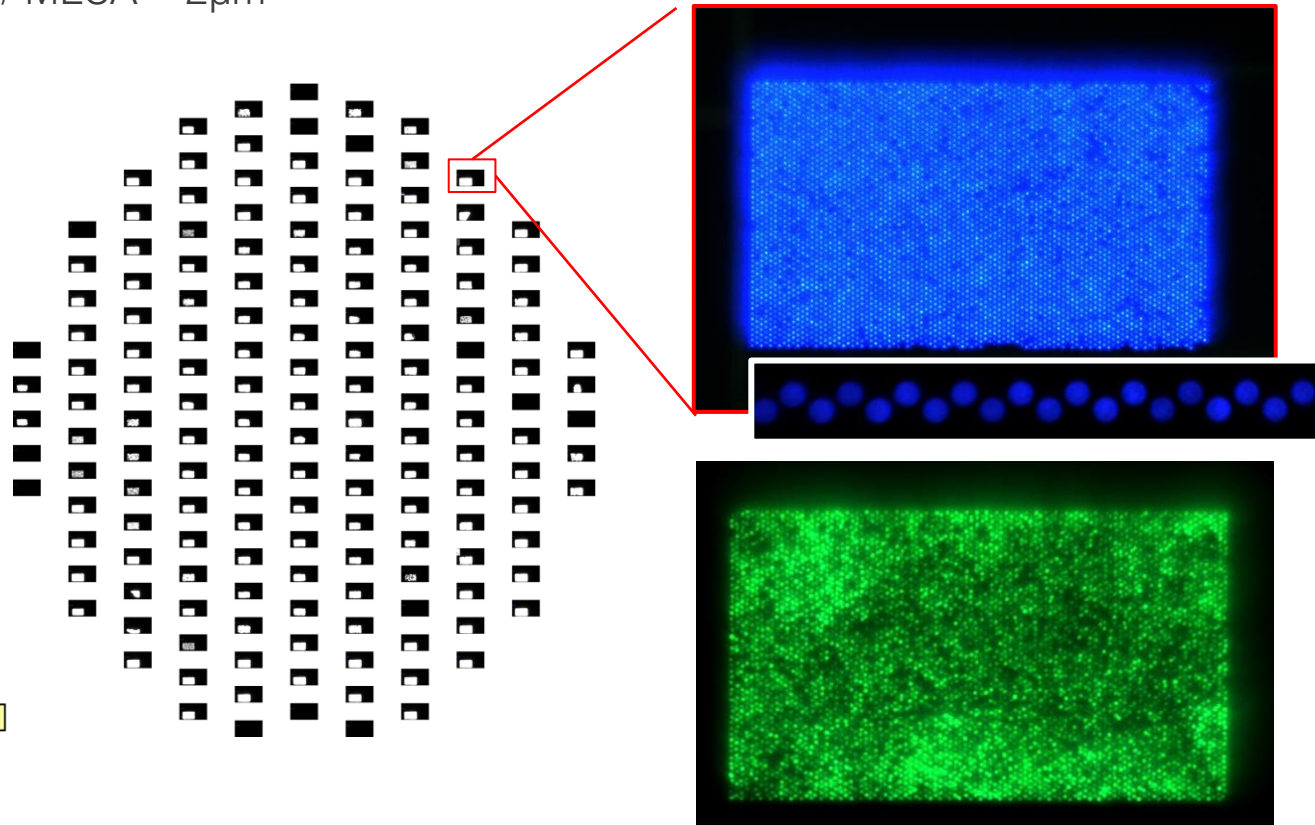
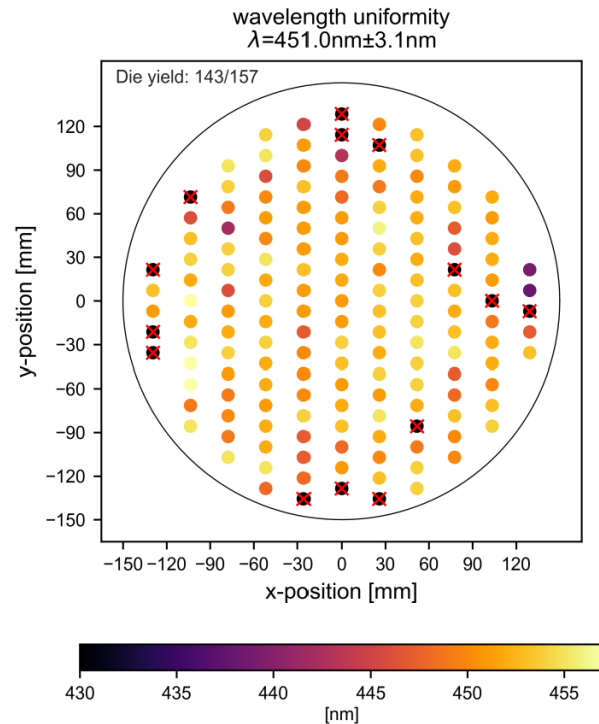


- W2W hybrid bonding of CMOS with GaN LED
 - Pixel pitch $3\mu\text{m}$ hexagon = 9150ppi
 - overlay variation < 200nm across 300mm wafer
 - No active CMOS in pathfinder lot; only passive matrix

WAFER MAPPING DATA

50 x 100 array with 3 μ m pitch / MESA = 2 μ m

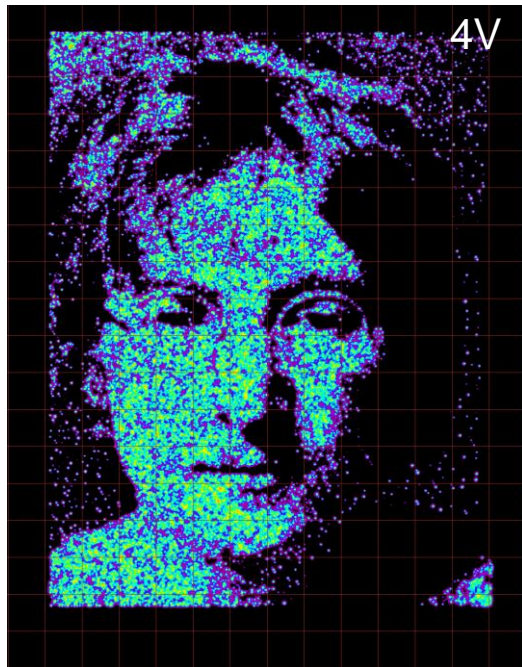
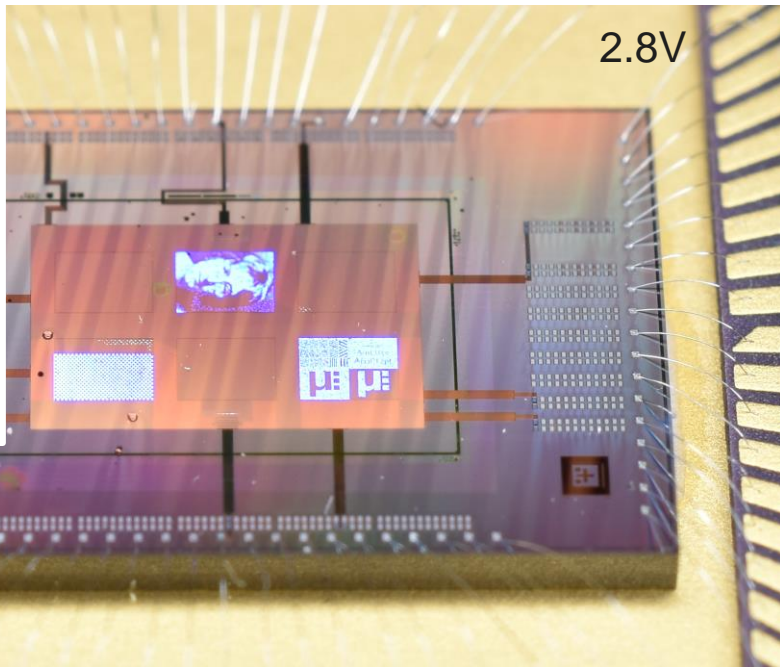
More than 90% of passive matrix test LED arrays lighten up



DISPLAY TEST STRUCTURES

480X320 PASSIVE MATRIX SUB-ARRAYS WITH 3UM PITCH

- >1Mnits @ 4V
- fill factor (up to 63%)

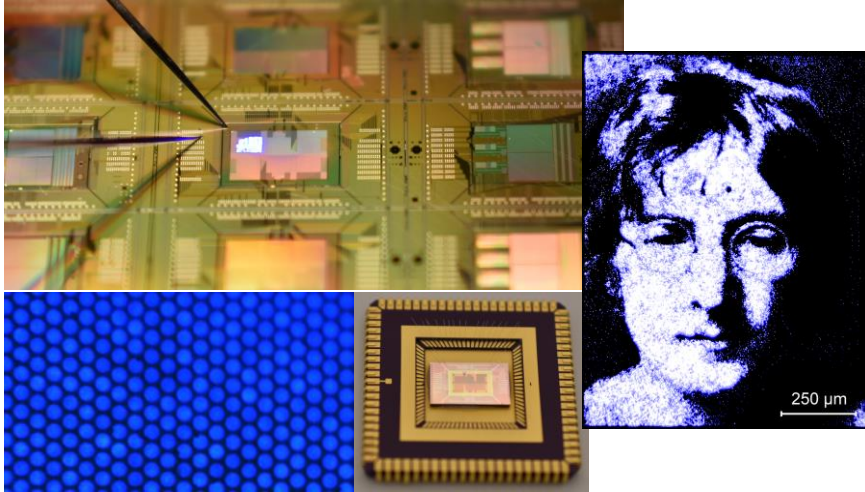


Radiance camera

ALL COLOR

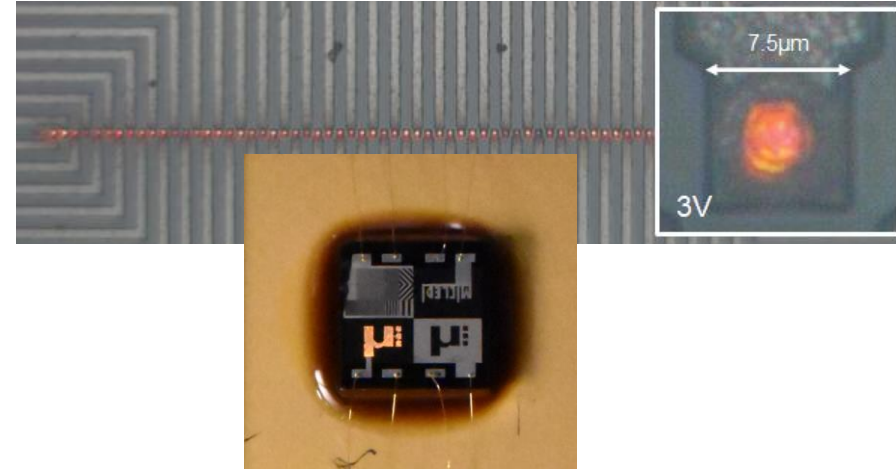
FIRST PRODUCT GENERATION: GAN ON SI FOR RGB

Devices for integration flow development



Design rule	MESA = 0.5-2.5 μm , Pitch = 3 μm hexagon, window=100%
Process flow	300mm GaN RC with W2W hybrid bonding;
Layout	passive matrix
Common potential	Anode
Outcoupling	Top emission; backside mirror + DBR; aperture =63%;

Devices for material and passivation characterization



Design rule	MESA = 3 μm , Pitch = 6 μm square, window=1.3 μm
Process flow	200mm GaN on Si ;
Layout	passive matrix
Common potential	Cathode
Outcoupling	Top emission; no backside mirror; aperture < 3.7%;

CONCLUSION



- Micledi has developed a solution to integrate tight pitched ($<3\mu\text{m}$) compound semiconductor with advanced 300mm Si-CMOS node for microLED arrays
- Proven process flow for passive $3\mu\text{m}$ pitch microLED array on 300mm full-automatic manufacturing tools (demo sample blue/green GaN LED available; blue GaN LED with wafer level optics Q3/2022; red GaN processing started)
- 300mm Foundry transfer started 

- This work was done in collaboration between MICLEDI and imec. We would like to acknowledge 3D and SAT department of imec, Imec 300mm pilot line and MICLEDI team Leuven
- Authors would like to acknowledge VLAIO O&O funding "MICLEDI"

